

**MPSH81**  
**PNP SILICON**  
**RF TRANSISTOR**



**TO-92 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR MPSH81 is a PNP Silicon Transistor designed for general purpose RF amplifier applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

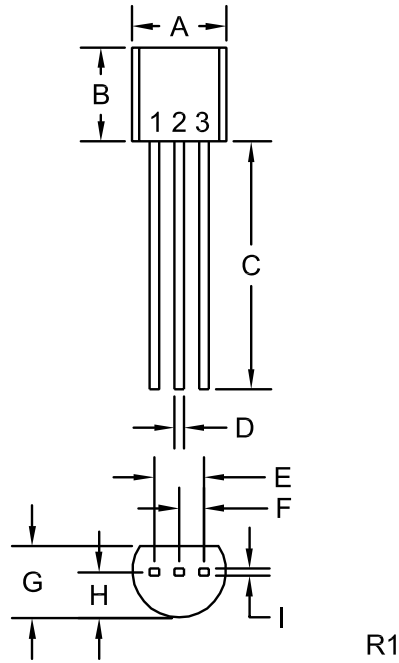
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
$V_{CB0}$	20	V
$V_{CEO}$	20	V
$V_{EBO}$	3.0	V
$I_C$	50	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\Theta_{JC}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=10\text{V}$		100	nA
$I_{EBO}$	$V_{EB}=2.0\text{V}$		100	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	20		V
$BV_{CEO}$	$I_C=1.0\text{mA}$	20		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	3.0		V
$V_{CE(SAT)}$	$I_C=5.0\text{mA}, I_B=0.5\text{mA}$		0.5	V
$V_{BE(ON)}$	$V_{CE}=10\text{V}, I_C=5.0\text{mA}$		0.9	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=5.0\text{mA}$	60		
$f_T$	$V_{CE}=10\text{V}, I_C=5.0\text{mA}, f=100\text{MHz}$	600		MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		0.85	pF
$C_{ib}$	$V_{CB}=10\text{V}, I_B=0, f=1.0\text{MHz}$		0.65	pF

TO-92 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

**LEAD CODE:**

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

**MARKING: FULL PART NUMBER**